

BZT52H series

Single Zener diodes in a SOD123F package

Rev. 01 — 22 December 2005

Product data sheet

1. Product profile

1.1 General description

General-purpose Zener diodes in a SOD123F small and flat lead Surface Mounted Device (SMD) plastic package.

1.2 Features

- Total power dissipation: ≤ 830 mW
- Small plastic package suitable for surface mounted design
- Wide working voltage range: nominal 2.4 V to 75 V (E24 range)
- Low differential resistance

1.3 Applications

- General regulation functions

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 10$ mA	[1] -	-	0.9	V
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[2] -	-	375	mW
			[3] -	-	830	mW

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

PHILIPS

2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	cathode		
2	anode		

sym001

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
BZT52H-C2V4 to BZT52H-C75	-	plastic surface mounted package; 2 leads	SOD123F

[1] The series consists of 37 types with nominal working voltages from 2.4 V to 75 V.

4. Marking

Table 4: Marking codes

Type number	Marking code	Type number	Marking code	Type number	Marking code
BZT52H-C2V4	B3	BZT52H-C8V2	BG	BZT52H-C30	BV
BZT52H-C2V7	B4	BZT52H-C9V1	BH	BZT52H-C33	BW
BZT52H-C3V0	B5	BZT52H-C10	BJ	BZT52H-C36	BX
BZT52H-C3V3	B6	BZT52H-C11	BK	BZT52H-C39	BY
BZT52H-C3V6	B7	BZT52H-C12	BL	BZT52H-C43	BZ
BZT52H-C3V9	B8	BZT52H-C13	BM	BZT52H-C47	C1
BZT52H-C4V3	B9	BZT52H-C15	BN	BZT52H-C51	C2
BZT52H-C4V7	BA	BZT52H-C16	BP	BZT52H-C56	C3
BZT52H-C5V1	BB	BZT52H-C18	BQ	BZT52H-C62	C4
BZT52H-C5V6	BC	BZT52H-C20	BR	BZT52H-C68	C5
BZT52H-C6V2	BD	BZT52H-C22	BS	BZT52H-C75	C6
BZT52H-C6V8	BE	BZT52H-C24	BT	-	-
BZT52H-C7V5	BF	BZT52H-C27	BU	-	-

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_F	forward current		-	250	mA
I_{ZSM}	non-repetitive peak reverse current		-	see Table 8 , 9 and 10	
P_{ZSM}	non-repetitive peak reverse power dissipation	[1]	-	40	W
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$ [2]	-	375	mW
		[3]	-	830	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

[1] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ °C}$ prior to surge

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	330 K/W
			[2]	-	-	150 K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[3]	-	-	70 K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

[3] Soldering point of cathode tab.

7. Characteristics

Table 7: Characteristics

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 10\text{ mA}$	[1]	-	0.9	V

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

Table 8: Characteristics per type; BZT52H-C2V4 to BZT52H-C24

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZT52H -Cxxx	Working voltage V_Z (V); $I_Z = 5\text{ mA}$		Maximum differential resistance r_{dif} (Ω)		Reverse current I_R (μA)		Temperature coefficient S_Z (mV/K); $I_Z = 5\text{ mA}$		Diode capacitance C_d (pF) [1]	Non-repetitive peak reverse current I_{ZSM} (A) [2]
	Min	Max	$I_Z = 1\text{ mA}$	$I_Z = 5\text{ mA}$	Max	V_R (V)	Min	Max	Max	Max
2V4	2.2	2.6	400	85	50	1	-3.5	0.0	450	6.0
2V7	2.5	2.9	500	83	20	1	-3.5	0.0	450	6.0
3V0	2.8	3.2	500	95	10	1	-3.5	0.0	450	6.0
3V3	3.1	3.5	500	95	5	1	-3.5	0.0	450	6.0
3V6	3.4	3.8	500	95	5	1	-3.5	0.0	450	6.0
3V9	3.7	4.1	500	95	3	1	-3.5	0.0	450	6.0
4V3	4.0	4.6	500	95	3	1	-3.5	0.0	450	6.0
4V7	4.4	5.0	500	78	3	2	-3.5	0.2	300	6.0
5V1	4.8	5.4	480	60	2	2	-2.7	1.2	300	6.0
5V6	5.2	6.0	400	40	1	2	-2.0	2.5	300	6.0
6V2	5.8	6.6	150	10	3	4	0.4	3.7	200	6.0
6V8	6.4	7.2	80	8	2	4	1.2	4.5	200	6.0
7V5	7.0	7.9	80	10	1	5	2.5	5.3	150	4.0
8V2	7.7	8.7	80	10	0.7	5	3.2	6.2	150	4.0
9V1	8.5	9.6	100	10	0.5	6	3.8	7.0	150	3.0
10	9.4	10.6	70	10	0.2	7	4.5	8.0	90	3.0
11	10.4	11.6	70	10	0.1	8	5.4	9.0	85	2.5
12	11.4	12.7	90	10	0.1	8	6.0	10.0	85	2.5
13	12.4	14.1	110	10	0.1	8	7.0	11.0	80	2.5
15	13.8	15.6	110	15	0.05	10.5	9.2	13.0	75	2.0
16	15.3	17.1	170	20	0.05	11.2	10.4	14.0	75	1.5
18	16.8	19.1	170	20	0.05	12.6	12.4	16.0	70	1.5
20	18.8	21.2	220	20	0.05	14	14.4	18.0	60	1.5
22	20.8	23.3	220	25	0.05	15.4	16.4	20.0	60	1.25
24	22.8	25.6	220	30	0.05	16.8	18.4	22.0	55	1.25

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$

[2] $t_p = 100\text{ }\mu\text{s}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

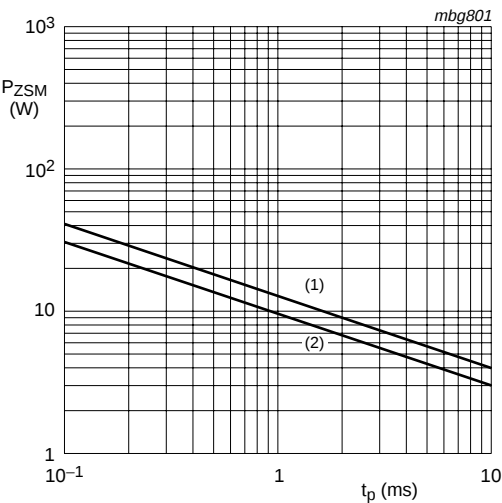
Table 9: Characteristics per type; BZT52H-C27 to BZT52H-C51 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZT52H -Cxxx	Working voltage V_Z (V); $I_Z = 2\text{ mA}$		Maximum differential resistance r_{dif} (Ω)		Reverse current I_R (μA)		Temperature coefficient S_Z (mV/K); $I_Z = 5\text{ mA}$		Diode capacitance C_d (pF) [1]	Non-repetitive peak reverse current I_{ZSM} (A) [2]
	Min	Max	$I_Z = 1\text{ mA}$	$I_Z = 5\text{ mA}$	Max	V_R (V)	Min	Max	Max	Max
27	25.1	28.9	250	40	0.05	18.9	21.4	25.3	50	1.0
30	28.0	32.0	250	40	0.05	21	24.4	29.4	50	1.0
33	31.0	35.0	250	40	0.05	23.1	27.4	33.4	45	0.9
36	34.0	38.0	250	60	0.05	25.2	30.4	37.4	45	0.8
39	37.0	41.0	300	75	0.05	27.3	33.4	41.2	45	0.7
43	40.0	46.0	325	80	0.05	30.1	37.6	46.6	40	0.6
47	44.0	50.0	325	90	0.05	32.9	42.0	51.8	40	0.5
51	48.0	54.0	350	100	0.05	35.7	46.6	57.2	40	0.4

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$ [2] $t_p = 100\text{ }\mu\text{s}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$ **Table 10: Characteristics per type; BZT52H-C56 to BZT52H-C75** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

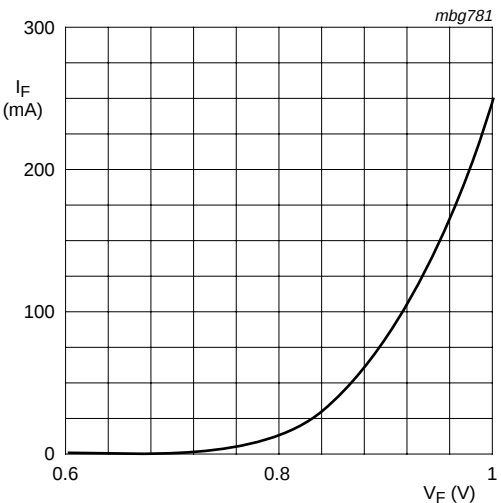
BZT52H -Cxxx	Working voltage V_Z (V); $I_Z = 2\text{ mA}$		Maximum differential resistance r_{dif} (Ω)		Reverse current I_R (μA)		Temperature coefficient S_Z (mV/K); $I_Z = 5\text{ mA}$		Diode capacitance C_d (pF) [1]	Non-repetitive peak reverse current I_{ZSM} (A) [2]
	Min	Max	$I_Z = 0.5\text{ mA}$	$I_Z = 2\text{ mA}$	Max	V_R (V)	Min	Max	Max	Max
56	52.0	60.0	375	120	0.05	39.2	52.2	63.8	40	0.3
62	58.0	66.0	400	140	0.05	43.4	58.8	71.6	35	0.3
68	64.0	72.0	400	160	0.05	47.6	65.6	79.8	35	0.25
75	70.0	79.0	400	175	0.05	52.5	73.4	88.6	35	0.20

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$ [2] $t_p = 100\text{ }\mu\text{s}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$



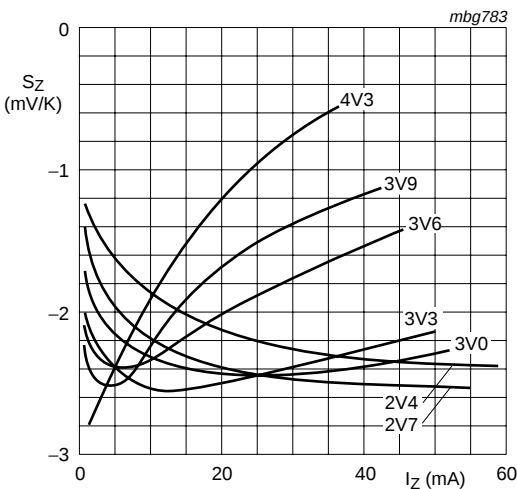
- (1) $T_j = 25^\circ\text{C}$ (prior to surge)
- (2) $T_j = 150^\circ\text{C}$ (prior to surge)

Fig 1. Non-repetitive peak reverse power dissipation as a function of pulse duration; maximum values



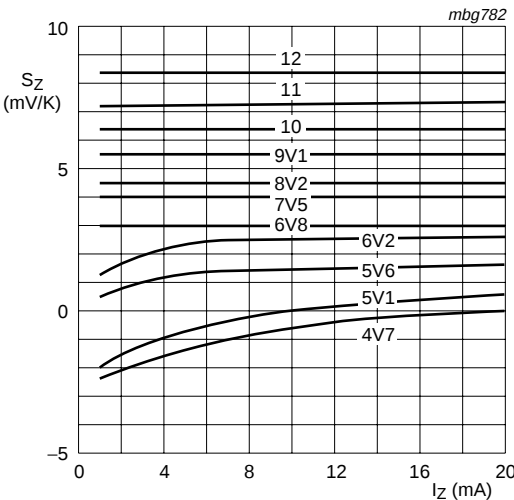
$T_j = 25^\circ\text{C}$

Fig 2. Forward current as a function of forward voltage; typical values



BZT52H-C2V4 to BZT52H-C4V3
 $T_j = 25^\circ\text{C}$ to 150°C

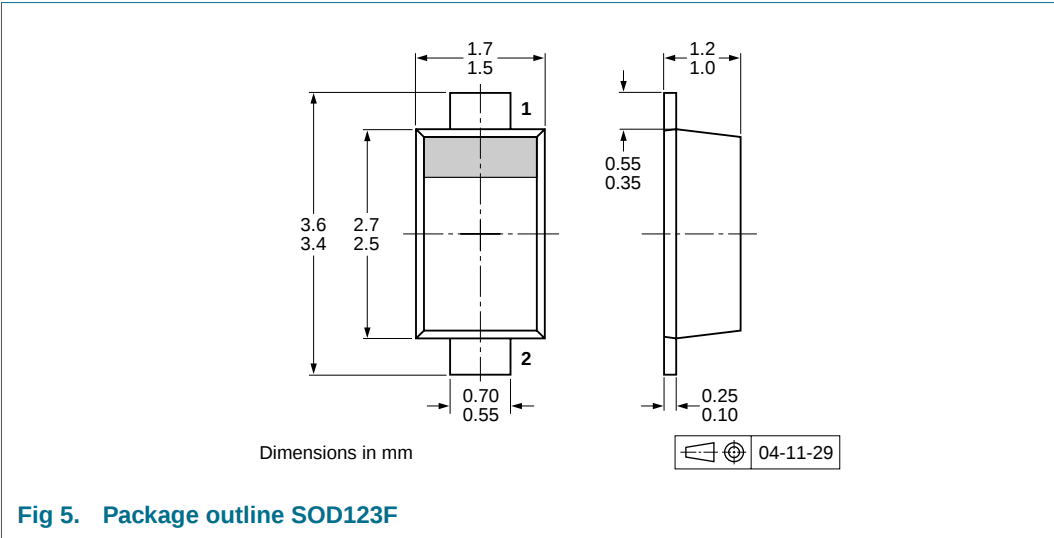
Fig 3. Temperature coefficient as a function of working current; typical values



BZT52H-C4V7 to BZT52H-C12
 $T_j = 25^\circ\text{C}$ to 150°C

Fig 4. Temperature coefficient as a function of working current; typical values

8. Package outline



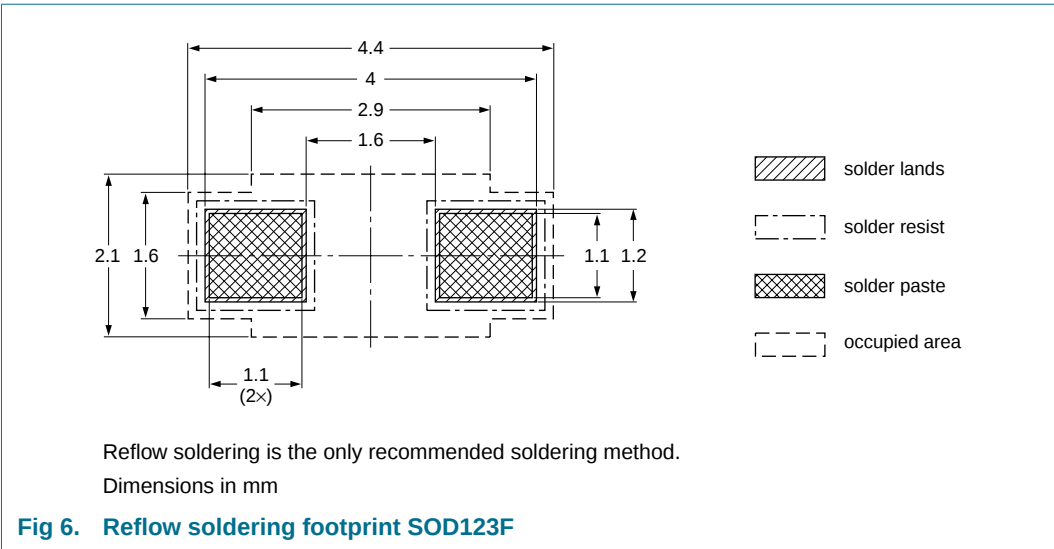
9. Packing information

Table 11: Packing methods
The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity	
			3000	10000
BZT52H-C2V4 to BZT52H-C75	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 16](#).

10. Soldering





11. Revision history

Table 12: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BZT52H_SER_1	20051222	Product data sheet	-	9397 750 15082	-

12. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

13. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

15. Trademarks

Notice — All referenced brands, product names, service names and trademarks are the property of their respective owners.

14. Disclaimers

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors

16. Contact information

For additional information, please visit: <http://www.semiconductors.philips.com>

For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com



17. Contents

1	Product profile	1
1.1	General description.	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data.	1
2	Pinning information.	2
3	Ordering information.	2
4	Marking	2
5	Limiting values.	3
6	Thermal characteristics.	3
7	Characteristics.	4
8	Package outline	7
9	Packing information.	7
10	Soldering	7
11	Revision history.	8
12	Data sheet status	9
13	Definitions	9
14	Disclaimers.	9
15	Trademarks.	9
16	Contact information	9





**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331